TO-92 Plastic-Encapsulate Transistors

KSP44 TRANSISTOR（ NPN ）

FEATURES

Power dissipation

P_{CM}: 0.625 W（Tamb=25℃）

Collector current

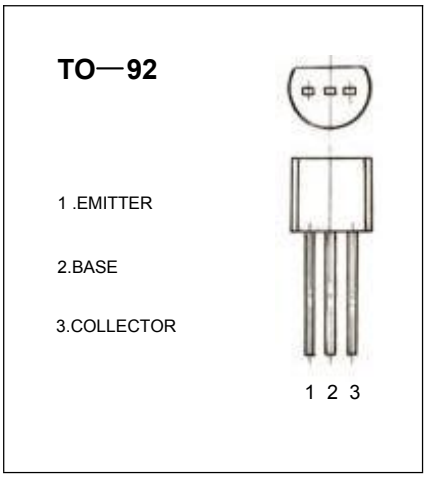
I_{CM}: 0.3 A

Collector-base voltage

$V_{(BR)CBO}$: 500 V

Operating and storage junction temperature range

T_J，T_{stg}: -55℃ to +150℃



ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	I_C=100μA, I_B=0	500			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C=1mA, I_B=0	400			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E=100μA, I_C=0	6.0			V
Collector cut-off current	I_{CBO}	V_{CB}=400V, I_E=0			0.1	μA
Collector cut-off current	I_{CBO}	V_{CE}=400V, I_B=0			0.5	μA
Emitter cut-off current	I_{CES}	V_{BE}= 4V, I_C=0			0.1	μA
DC current gain(note)	H_{FE}（1）	V_{CE}=10V, I_C=1mA	40			
DC current gain(note)	H_{FE}（2）	V_{CE}=10V, I_C=10mA	50		200	
DC current gain(note)	H_{FE}（3）	V_{CE}=10V, I_C=50mA	45			
DC current gain(note)	H_{FE}（4）	V_{CE}=10V, I_C=100mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=10mA, I_B=1mA			0.5	V
Base-emitter voltage	V_{BE}	I_B=1mA, I_C=10mA			0.75	V

CLASSIFICATION OF

HFE

Rank	1	2
Range	40-100	100-200